

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|-------|------------------|
| 1 | 795 | 438/682 | USPAT | 2004/05/24 16:57 |
| 2 | 485 | 438/681 | USPAT | 2004/05/24 16:57 |
| 3 | 962 | 438/683 | USPAT | 2004/05/24 16:57 |
| 4 | 288 | 438/684 | USPAT | 2004/05/24 16:58 |
| 5 | 998 | 438/680 | USPAT | 2004/05/24 16:58 |
| 6 | 777 | 438/649 | USPAT | 2004/05/24 16:58 |
| 7 | 259 | 438/650 | USPAT | 2004/05/24 16:58 |
| 8 | 259 | 438/651 | USPAT | 2004/05/24 16:58 |
| 9 | 1194 | 438/655 | USPAT | 2004/05/24 16:58 |
| 10 | 1273 | 438/656 | USPAT | 2004/05/24 16:58 |
| 11 | 460 | 438/657 | USPAT | 2004/05/24 16:58 |
| 12 | 370 | 438/668 | USPAT | 2004/05/24 16:58 |
| 13 | 262 | 438/721 | USPAT | 2004/05/24 16:58 |
| 14 | 99 | 438/755 | USPAT | 2004/05/24 16:58 |
| 15 | 266 | 438/510 | USPAT | 2004/05/24 16:58 |
| 16 | 647 | 438/514 | USPAT | 2004/05/24 16:59 |
| 17 | 76 | 438/914 | USPAT | 2004/05/24 16:59 |
| 18 | 151 | 438/954 | USPAT | 2004/05/24 16:59 |
| 19 | 1283 | 438/197 | USPAT | 2004/05/24 16:59 |
| 20 | 494 | 438/276 | USPAT | 2004/05/24 16:59 |
| 21 | 810 | 438/300 | USPAT | 2004/05/24 16:59 |
| 22 | 1779 | 438/301 | USPAT | 2004/05/24 16:59 |
| 23 | 1859 | 438/303 | USPAT | 2004/05/24 16:59 |
| 24 | 406 | 438/304 | USPAT | 2004/05/24 16:59 |
| 25 | 332 | 438/311 | USPAT | 2004/05/24 16:59 |
| 26 | 215 | 438/733 | USPAT | 2004/05/24 16:59 |
| - | 0 | 10/700779 | USPAT | 2004/05/24 11:15 |
| - | 0 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and salicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:20 |
| - | 0 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:21 |
| - | 0 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and gap and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:24 |
| - | 0 | ILD and dielectric and electrode and gate and spacer and side and wall and silicide and salicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:24 |
| - | 1 | ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:23 |
| - | 1 | | USPAT | 2004/05/24 11:23 |
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| - | 1 | ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:24 |
| - | 1 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:24 |

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| - | 1 | | USPAT | 2004/05/24 11:26 |
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| - | 1 | | USPAT | 2004/05/24 11:27 |
| - | 1 | ("5751040").PN. | USPAT | 2004/05/24 11:27 |
| - | 1 | ("4994404").PN. | USPAT | 2004/05/24 11:27 |
| - | 1 | ("6365943").PN. | USPAT | 2004/05/24 11:27 |
| - | 1 | ("6380535").PN. | USPAT | 2004/05/24 11:28 |
| - | 1 | ("6455373").PN. | USPAT | 2004/05/24 11:28 |
| - | 1 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:29 |
| - | 0 | ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped | USPAT | 2004/05/24 11:29 |
| - | 1 | (ILD and interlevel and dielectric and electrode and gate and spacer and side and wall and gap and gaps and silicide and source and drain and polysilicon and thickness and ion and p-type and n-type and channel and region and LDD and lightly and doped) and (sidewall or spacer or gap or gaps or void or closely or thickness or cobalt or nickel or titanium or polysilicon or contact or area or region or rate or aspect or ratio or silicide or silicide or n-type or p-type or channel or lightly or doped or LDD or etch or anisotropically or back or angstroms) | USPAT | 2004/05/24 16:57 |
| - | 1 | (ILD and dielectric and electrode and gate and spacer and side and wall and silicide and source and drain and polysilicon and thickness and ion and void and channel and region and LDD and lightly and doped) and (sidewall or spacer or gap or gaps or void or closely or thickness or cobalt or nickel or titanium or polysilicon or contact or area or region or rate or aspect or ratio or silicide or silicide or n-type or p-type or channel or lightly or doped or LDD or etch or anisotropically or back or angstroms) | USPAT | 2004/05/24 11:38 |

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